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		Application Number			
		Filing Date	Concurrently Herewith		
		First Named Inventor	Rama I. Hegde		
		Group Art Unit			
Sheet	1	of	2	Examiner Name	
				Attorney Docket Number	SC11697TP

10/09/06  
 10/09/06  
 03/15/02

U. S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number Code <sup>2</sup>	Kind (if known)			
AKS	AA	6,235,594 B1		Merchant et al.	05-22-2001	
AKS	AB	2001/0024387 A1		Raaijmakers et al.	02-27-2001	
AICS	AC	2001/0013629 A1		Bai	08-16-2001	
AICS	AD	5,885,877		Gardner et al.	03-23-1999	
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AKS	AG	5,153,701		Roy	10-06-1992	
AKS	AH	6,090,686		Brady et al.	07-18-2000	

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
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Examiner Signature	Asst. Examiner Sachar	Date Considered	3/21/03
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**OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
AKS	AI	D. Prot et al., "Self-diffusion in $\alpha$ -Al <sub>2</sub> O <sub>3</sub> IL Oxygen diffusion in 'undoped' single crystals", 1996 Taylor & Francis Ltd., Philosophical Magazine A, 1996, Volume 73, No. 4, pgs 899-917.	
AKS	AJ	H. Bender et al., "Physical Characterisation of High-k Gate Stacks Deposited on HF-Last Surfaces", IWGI 3002, Tokyo, pgs. 1-7.	
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AKS	AL	L. Manchanda et al., "Multi-component high-K gate dielectrics for the silicon industry", Elsevier Science B.V., pgs. 351-359.	
AKS	AM	V.V. Afanas'ev <sup>a</sup> et al., "Energy barriers between (100)Si and Al <sub>2</sub> O <sub>3</sub> and ZrO <sub>2</sub> -based dielectric stacks: internal electron photoemission measurements", 2001 Elsevier Science B.V. All rights reserved, pgs. 335-339.	
AKS	AN	Massimo Fischetti et al., "IBM Research Report", RC 22092 (99048) June 12, 2001, pgs. 1-25.	
AKS	AO	D.A. Neumayer et al., "Materials characterization of ZrO <sub>2</sub> -SiO <sub>2</sub> and HfO <sub>2</sub> -SiO <sub>2</sub> binary oxides deposited by chemical solution deposition", 2001 American Institute of Physics, Journal of Applied Physics, Vol. 90, No. 4, August 15, 2001, pgs. 1801-1808.	
AKS	AP	Toyokazu Tambo et al., "Molecular Beam Epitaxy of SrTiO <sub>3</sub> Films on Si(100)-2x1 with SrO Buffer Layer", 1998 Publication Board, Japanese Journal of Applied Physics, Jpn. J. Appl. Phys. Vol. 37 (1998), pgs 4454-4459.	

Examiner Signature	Asish Kumar Sarker	Date Considered	3/21/03
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